

3Q Hi-Com Triac Rev. 02 — 12 April 2011

Product data sheet

1. Product profile

1.1 General description

Planar passivated high commutation triac in a SOT78 plastic package intended for use in circuits where high static and dynamic dV/dt and high dl/dt can occur. This "series B" triac will commutate the full rated RMS current at the maximum rated junction temperature without the aid of a snubber.

1.2 Features and benefits

- 3Q technology for improved noise immunity
- High commutation capability with maximum false trigger immunity
- High immunity to false turn-on by dV/dt

1.3 Applications

- Electronic thermostats
- General purpose motor controls

- High voltage capability
- Planar passivated for voltage ruggedness and reliability
- Triggering in three quadrants only
- Rectifier-fed DC inductive loads e.g. DC motors and solenoids

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
V _{DRM}	repetitive peak off-state voltage		-	-	600	V
I _{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25 \text{ °C};$ $t_p = 20 \text{ ms}; \text{ see } Figure 4;$ see Figure 5	-	-	65	A
I _{T(RMS)}	RMS on-state current	full sine wave; T _{mb} ≤ 102 °C; see <u>Figure 1</u> ; see <u>Figure 2</u> ; see <u>Figure 3</u>	-	-	8	A
Static cha	racteristics					
I _{GT}	gate trigger current	$V_D = 12 V; I_T = 0.1 A; T2+G+;$ $T_j = 25 °C; see Figure 7$	2	18	50	mA
		V _D = 12 V; I _T = 0.1 A; T2+ G-; T _j = 25 °C; see <u>Figure 7</u>	2	21	50	mA
		V _D = 12 V; I _T = 0.1 A; T2- G-; T _j = 25 °C; see <u>Figure 7</u>	2	34	50	mA
-						



2. Pinning information

Table 2.	Pinning	j information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1		N. 1
2	T2	main terminal 2	mb	T2-T1
3	G	gate		Sym051
mb	Τ2	mounting base; main terminal 2		

SOT78 (TO-220AB)

 $\begin{bmatrix} 1 & 2 & 1 \\ 1 & 2 & 3 \end{bmatrix}$

3. Ordering information

Table 3.Ordering information

Type number	Package		
	Name	Description	Version
BTA208-600B	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

4. Limiting values

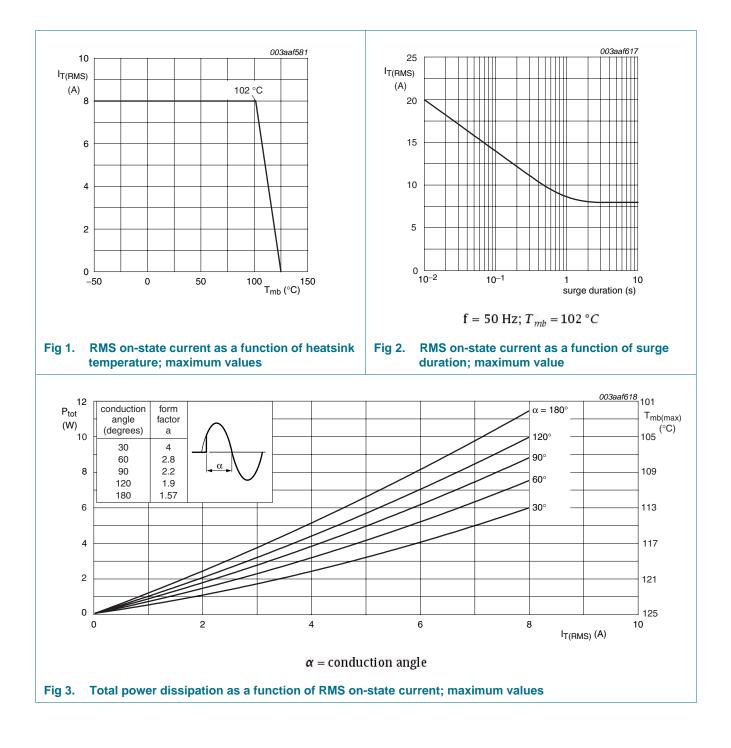
Table 4.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Мах	Unit
V _{DRM}	repetitive peak off-state voltage		-	600	V
I _{T(RMS)}	RMS on-state current	full sine wave; $T_{mb} \le 102 \text{ °C}$; see Figure 1; see Figure 2; see Figure 3	-	8	А
I _{TSM}	non-repetitive peak on-state current	full sine wave; T _{j(init)} = 25 °C; t _p = 20 ms; see <u>Figure 4</u> ; see <u>Figure 5</u>	-	65	А
		full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 16.7 \text{ ms}$	-	71	А
l ² t	l ² t for fusing	t _p = 10 ms; sine-wave pulse	-	21	A ² s
dl _T /dt	rate of rise of on-state current	$I_T = 12 \text{ A}; I_G = 0.2 \text{ A}; dI_G/dt = 0.2 \text{ A}/\mu \text{s}$	-	100	A/µs
I _{GM}	peak gate current		-	2	А
V _{GM}	peak gate voltage		-	5	V
P _{GM}	peak gate power		-	5	W
P _{G(AV)}	average gate power	over any 20 ms period	-	0.5	W
T _{stg}	storage temperature		-40	150	°C
Tj	junction temperature		-	125	°C

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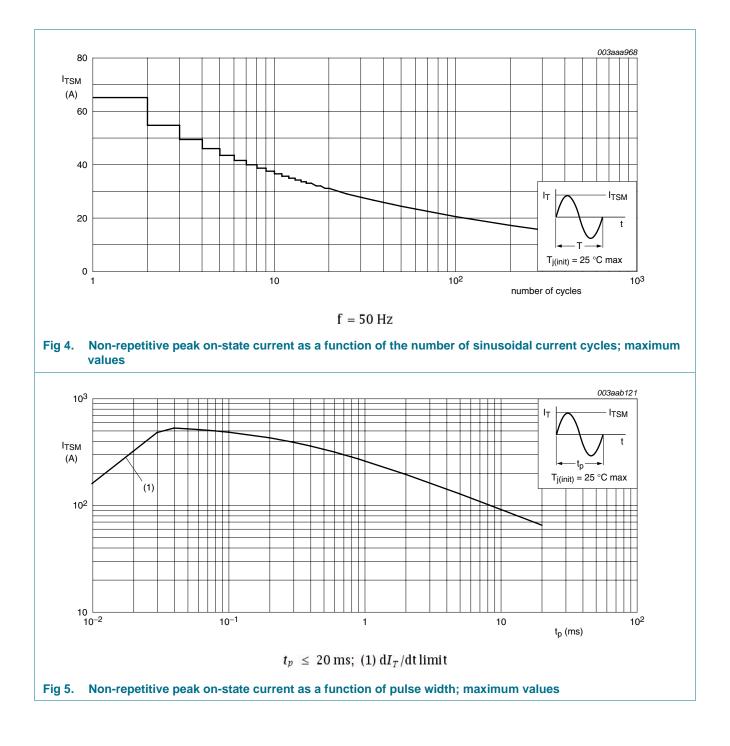
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5. Thermal characteristics

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Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	full cycle; see Figure 6	-	-	2	K/W
		half cycle; see Figure 6	-	-	2.4	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	-	60	-	K/W

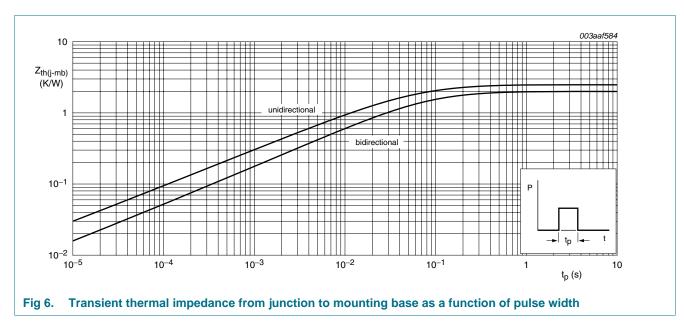


Table 5. Thermal characteristics

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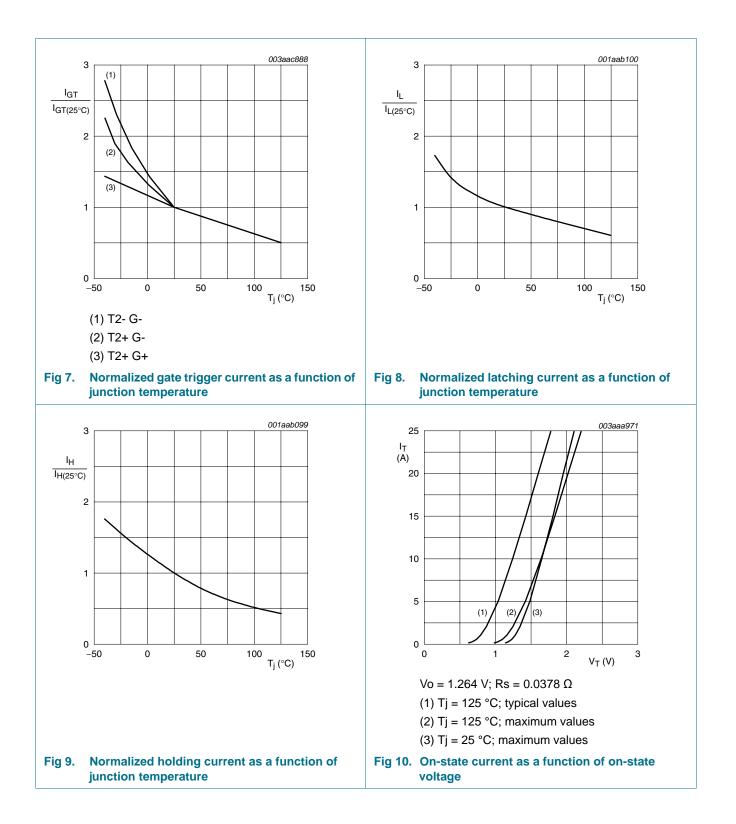
6. Characteristics

Characteristics					
Parameter	Conditions	Min	Тур	Max	Unit
aracteristics					
gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; \text{ T2+ G+}; \text{T}_j = 25 \text{ °C};$ see <u>Figure 7</u>	2	18	50	mA
	$V_D = 12 \text{ V}; \text{ I}_T = 0.1 \text{ A}; \text{ T2+ G-}; \text{ T}_j = 25 \text{ °C};$ see <u>Figure 7</u>	2	21	50	mA
	$V_D = 12 \text{ V}; \text{ I}_T = 0.1 \text{ A}; \text{ T2- G-}; \text{ T}_j = 25 \text{ °C};$ see Figure 7	2	34	50	mA
latching current	V _D = 12 V; I _G = 0.1 A; T2+ G+; T _j = 25 °C; see <u>Figure 8</u>	-	31	60	mA
	$V_D = 12 \text{ V}; \text{ I}_G = 0.1 \text{ A}; \text{ T2+ G-}; \text{ T}_j = 25 \text{ °C};$ see Figure 8	-	34	90	mA
	$V_D = 12 \text{ V}; \text{ I}_G = 0.1 \text{ A}; \text{ T2- G-}; \text{ T}_j = 25 \text{ °C};$ see Figure 8	-	30	60	mA
holding current	V _D = 12 V; T _j = 25 °C; see <u>Figure 9</u>	-	31	60	mA
on-state voltage	I _T = 10 A; T _j = 25 °C; see <u>Figure 10</u>	-	1.3	1.65	V
gate trigger voltage	V _D = 12 V; I _T = 0.1 A; T _j = 25 °C; see <u>Figure 11</u>	-	0.7	1.5	V
	$V_D = 400 \text{ V}; I_T = 0.1 \text{ A}; T_j = 125 \text{ °C};$ see Figure 11	0.25	0.4	-	V
off-state current	V _D = 600 V; T _j = 125 °C	-	0.1	0.5	mA
characteristics					
rate of rise of off-state voltage	V_{DM} = 402 V; T_j = 125 °C; exponential waveform; gate open circuit	1000	4000	-	V/µs
rate of change of commutating current	$V_D = 400 \text{ V}; \text{ T}_j = 125 \text{ °C}; \text{ I}_{T(RMS)} = 8 \text{ A};$ $dV_{com}/dt = 20 \text{ V/}\mu\text{s};$ gate open circuit; snubberless condition; see <u>Figure 12</u>	-	14	-	A/ms
gate-controlled turn-on time	I_{TM} = 12 A; V_D = 600 V; I_G = 0.1 A; dI_G/dt = 5 A/µs	-	2	-	μs
	Parameter aracteristics gate trigger current latching current holding current on-state voltage gate trigger voltage off-state current characteristics rate of rise of off-state voltage rate of change of commutating current gate-controlled turn-on	ParameterConditionsaracteristicsgate trigger current $V_D = 12 \ V; \ I_T = 0.1 \ A; \ T2+ \ G+; \ T_j = 25 \ ^{\circ}C;$ see Figure 7 $V_D = 12 \ V; \ I_T = 0.1 \ A; \ T2+ \ G-; \ T_j = 25 \ ^{\circ}C;$ see Figure 7 $V_D = 12 \ V; \ I_T = 0.1 \ A; \ T2+ \ G-; \ T_j = 25 \ ^{\circ}C;$ see Figure 7latching current $V_D = 12 \ V; \ I_G = 0.1 \ A; \ T2+ \ G+; \ T_j = 25 \ ^{\circ}C;$ see Figure 8 $V_D = 12 \ V; \ I_G = 0.1 \ A; \ T2+ \ G+; \ T_j = 25 \ ^{\circ}C;$ see Figure 8 $V_D = 12 \ V; \ I_G = 0.1 \ A; \ T2+ \ G-; \ T_j = 25 \ ^{\circ}C;$ see Figure 8 $V_D = 12 \ V; \ I_G = 0.1 \ A; \ T2- \ G-; \ T_j = 25 \ ^{\circ}C;$ see Figure 8holding current $V_D = 12 \ V; \ T_j = 25 \ ^{\circ}C;$ see Figure 9on-state voltage $I_T = 10 \ A; \ T_j = 25 \ ^{\circ}C;$ see Figure 9on-state voltage $V_D = 12 \ V; \ I_T = 0.1 \ A; \ T_j = 25 \ ^{\circ}C;$ see Figure 11off-state current $V_D = 600 \ V; \ T_j = 125 \ ^{\circ}C;$ see Figure 11off-state current $V_D = 600 \ V; \ T_j = 125 \ ^{\circ}C;$ see Figure 11off-state current $V_D = 402 \ V; \ T_j = 125 \ ^{\circ}C;$ see Figure 12rate of rise of off-state commutating current $V_D = 400 \ V; \ T_j = 125 \ ^{\circ}C;$ subberless condition; see Figure 12gate-controlled turn-on $I_{TM} = 12 \ A; \ V_D = 600 \ V; \ I_G = 0.1 \ A;$	$\begin{array}{ c c c c c } \hline \mbox{Parameter} & \mbox{Conditions} & \mbox{Min} \\ \hline \mbox{practeristics} \\ \hline \mbox{gate trigger current} & V_D = 12 V; I_T = 0.1 A; T2+ G+; T_j = 25 °C; & 2 \\ \hline \mbox{see Figure 7} & V_D = 12 V; I_T = 0.1 A; T2+ G-; T_j = 25 °C; & 2 \\ \hline \mbox{see Figure 7} & V_D = 12 V; I_T = 0.1 A; T2- G-; T_j = 25 °C; & 2 \\ \hline \mbox{see Figure 7} & V_D = 12 V; I_G = 0.1 A; T2+ G+; T_j = 25 °C; & - \\ \hline \mbox{see Figure 8} & V_D = 12 V; I_G = 0.1 A; T2+ G-; T_j = 25 °C; & - \\ \hline \mbox{see Figure 8} & V_D = 12 V; I_G = 0.1 A; T2- G-; T_j = 25 °C; & - \\ \hline \mbox{see Figure 8} & V_D = 12 V; I_G = 0.1 A; T2- G-; T_j = 25 °C; & - \\ \hline \mbox{see Figure 8} & V_D = 12 V; I_G = 0.1 A; T2- G-; T_j = 25 °C; & - \\ \hline \mbox{see Figure 8} & V_D = 12 V; I_J = 25 °C; see Figure 9 & - \\ \hline \mbox{on-state voltage} & I_T = 10 A; T_j = 25 °C; see Figure 9 & - \\ \hline \mbox{on-state voltage} & I_T = 10 A; T_j = 25 °C; see Figure 10 & - \\ \hline \mbox{gate trigger voltage} & V_D = 12 V; I_T = 0.1 A; T_j = 25 °C; & - \\ \hline \mbox{see Figure 11} & V_D = 400 V; I_T = 0.1 A; T_j = 125 °C; & - \\ \hline \mbox{see Figure 11} & V_D = 600 V; T_j = 125 °C; exponential voltage & V_D = 400 V; T_j = 125 °C; exponential voltage & V_D = 400 V; T_j = 125 °C; exponential voltage & V_D = 400 V; T_j = 125 °C; exponential voltage & V_D = 400 V; T_j = 125 °C; HT(RMS) = 8 A; \\ \hline \mbox{voltage} & V_D = 400 V; T_j = 125 °C; HT(RMS) = 8 A; \\ \hline \mbox{voltage of commutating current} & V_D = 400 V; I_G = 0.0 V; I_G = 0.1 A; & - \\ \hline \mbox{voltage of commutating current} & I_{TM} = 12 A; V_D = 600 V; I_G = 0.1 A; & - \\ \hline \mbox{voltage one circuit} & - \\ \hline \mbox{voltage one circuit} & - \\ \hline \mbox{voltage one circuit} & - \\ \hline \mbox{voltage} & V_D = 400 V; T_J = 125 °C; HT(RMS) = 8 A; \\ \hline \mbox{voltage one circuit} & - \\ \hline voltage one ci$	$\begin{array}{ c c c c c c c } \hline Parameter & Conditions & Min & Typ \\ \hline \mbox{aracteristics} & & & & & & & & & & & & & & & & & & &$	$\begin{tabular}{ c c c c c } \hline Parameter & Conditions & Min & Typ & Max \\ \hline \mbox{aracteristics} & & & & & & & & & & & & & & & & & & &$

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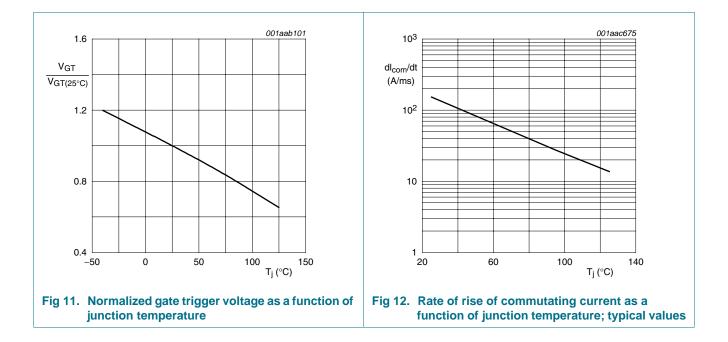
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Package outline 7.

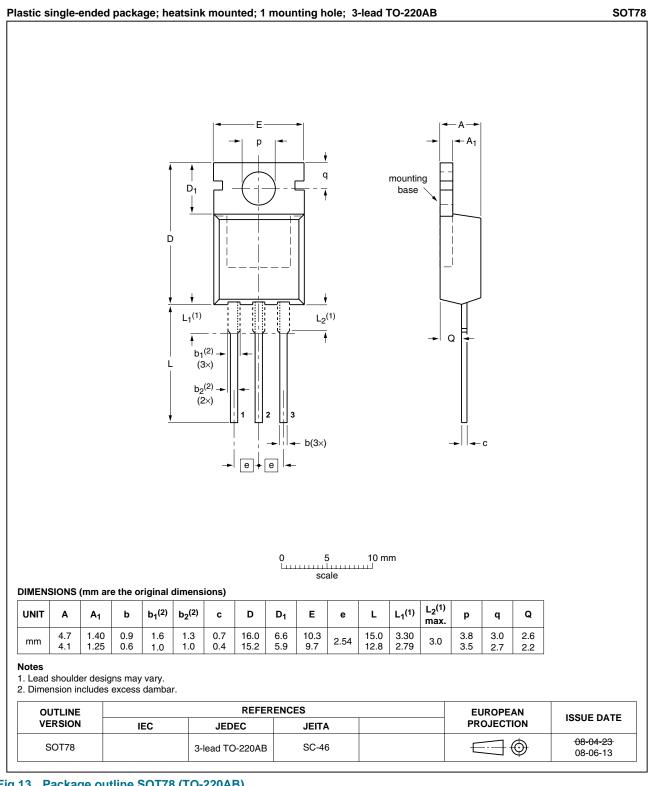


Fig 13. Package outline SOT78 (TO-220AB)

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BTA208-600B

8. Revision history

Table 7. Revision histo	ry			
Document ID	Release date	Data sheet status	Change notice	Supersedes
BTA208-600B v.2	20110412	Product data sheet	-	BTA208_SERIES_B v.1
Modifications:		this data sheet has been IXP Semiconductors.	redesigned to compl	ly with the new identity
	 Legal texts have 	ve been adapted to the ne	ew company name v	where appropriate.
	 Type number I 	BTA208-600B separated	from data sheet BTA	208_SERIES_B v.1.
BTA208_SERIES_B v.1	19970901	Product specification	-	-

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9. Legal information

9.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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